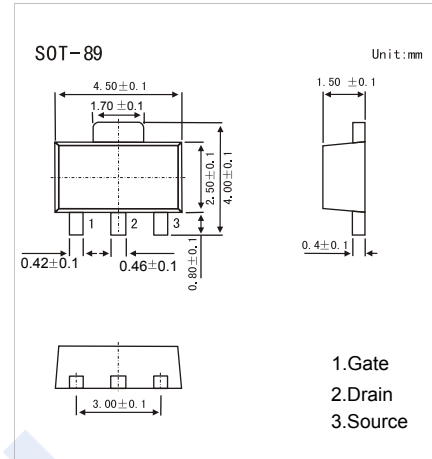
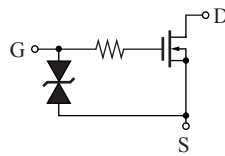


N-Channel MOSFET 2SK2211

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 1A$
- $R_{DS(ON)} < 0.75 \Omega$ ($V_{GS} = 4V$)
- $R_{DS(ON)} < 0.6 \Omega$ ($V_{GS} = 10V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	1	A
Pulsed Drain Current	I_{DM}	2	
Power Dissipation	P_D	1	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = 100 \mu A, V_{GS} = 0V$	30			V
Gate to Source voltage	V_{GSS}	$I_{GS} = 100 \mu A, V_{DS} = 0V$	± 20			
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 25V, V_{GS} = 0V$			10	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 15V$			± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 5V, I_D = 1mA$	0.8		2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4V, I_D = 0.5A$			0.75	Ω
		$V_{GS} = 10V, I_D = 0.5A$			0.6	
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 0.5A$	0.5			S
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$		87		pF
Output Capacitance	C_{oss}			69		
Reverse Transfer Capacitance	C_{rss}			23		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 10V, I_D = 0.5A, R_L = 10 \Omega$		12		ns
Turn-Off DelayTime	$t_{d(off)}$			60		
Turn-Off Fall Time	t_f			160		

■ Marking

Marking	2M
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N-Channel MOSFET 2SK2211

■ Typical Characteristics

